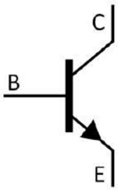
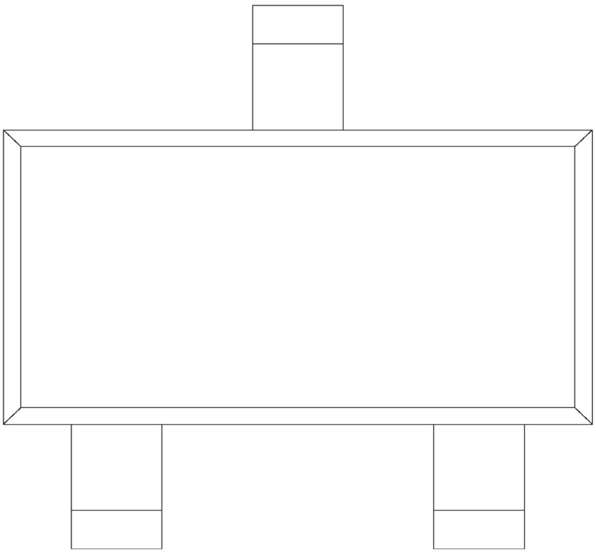
SOT-323 NPN Silicon NPN transistor in



Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	50	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=50μA	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=50μA	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=24V			0.5	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=3.0V			0.5	μA
DC Current Gain	h_{FE}	V_{CE}=6.0V I_C=1.0mA	56		270	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=10mA I_B=1.0mA		0.1	0.3	V
Transition Frequency	f_T	V_{CE}=6.0V I_C=1.0mA f=100MHz	150	300		MHz
Collector output capacitance	C_{ob}	V_{CB}=6.0V I_E=0 f=1.0MHz		1.3	2.2	pF



H

A

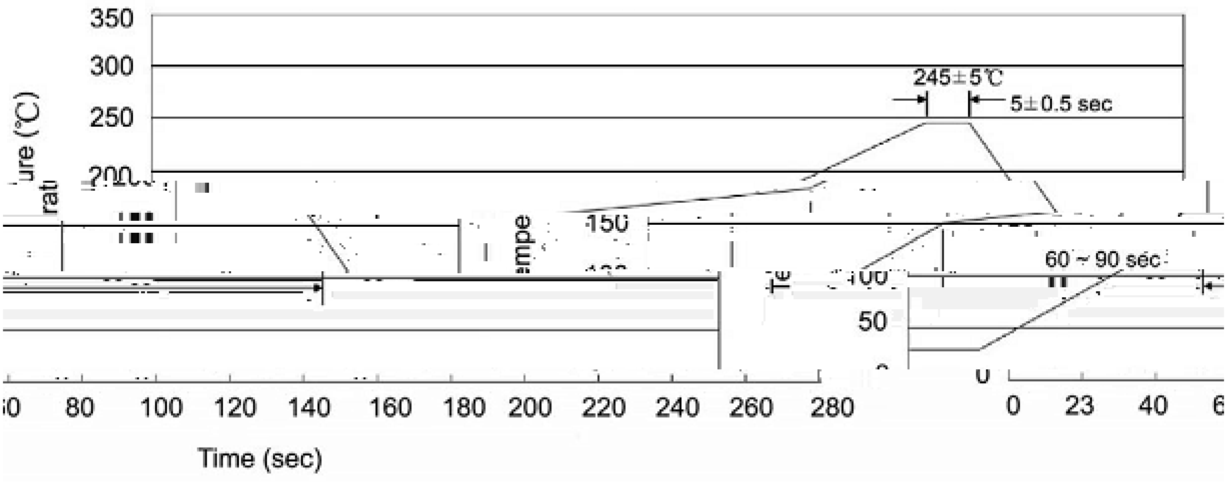
N hFE

Note:

H: Company Code.

A: Product Type.

N h_{FE}



1 25 150 60 90sec;

2 245±5 5±0.5sec;

3 2 10 /sec.

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-323	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205